

MOSFET – POWERTRENCH[®], N-Channel Shielded Gate

80 V, 123 A, 4.3 mΩ

FDMS4D4N08C

Description

This N-Channel MV MOSFET is produced using onsemi's advanced POWERTRENCH process that incorporates Shielded Gate technology. This process has been optimized to minimise on-state resistance and yet maintain superior switching performance with best in class soft body diode.

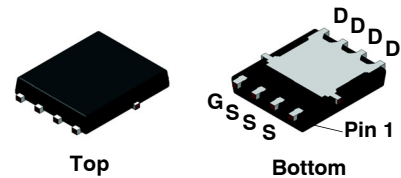
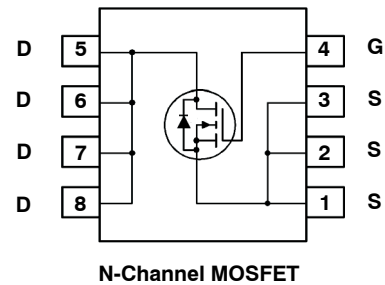
Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 4.3 mΩ at $V_{GS} = 10$ V, $I_D = 44$ A
- Max $r_{DS(on)}$ = 10.4 mΩ at $V_{GS} = 6$ V, $I_D = 22$ A
- 50% Lower Q_{rr} than Other MOSFET Suppliers
- Lowers Switching Noise/EMI
- MSL1 Robust Package Design
- 100% UIL Tested
- RoHS Compliant

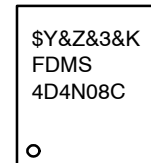
Typical Applications

- Primary DC–DC MOSFET
- Synchronous Rectifier in DC–DC and AC–DC
- Motor Drive
- Solar

ELECTRICAL CONNECTION



MARKING DIAGRAM



\$Y	= onsemi Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FDMS4D4N08C	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDMS4D4N08C

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, Unless otherwise specified)

Symbol	Parameter	Ratings	Unit
V_{DS}	Drain to Source Voltage	80	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current –Continuous $T_C = 25^\circ\text{C}$ (Note 5)	123	A
	–Continuous $T_C = 100^\circ\text{C}$ (Note 5)	78	
	–Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	17	
	–Pulsed (Note 4)	498	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	486	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	125	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to $+150$	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Shipping [†]
FDMS4D4N08C	FDMS4D4N08C	PQFN8 5x6 (Pb-Free/Halogen Free)	3000 Units/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C		63		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 64 V, V _{GS} = 0 V			1	μA
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA

ON CHARACTERISTICS (Note NO TAG)

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	2.0	3.0	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C		-8.2		mV/°C
r _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 44 A		3.7	4.3	mΩ
		V _{GS} = 6 V, I _D = 22 A		5.7	10.4	
		V _{GS} = 10 V, I _D = 44 A, T _J = 125°C		5.9	7.2	
g _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 44 A		98		S

DYNAMIC CHARACTERISTICS

C _{ISS}	Input Capacitance	V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz		2920	4090	pF
C _{OSS}	Output Capacitance			1045	1465	
C _{RSS}	Reverse Transfer Capacitance			35	50	
R _G	Gate Resistance		0.1	1.3	2.5	Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn – On Delay Time	V _{DD} = 40 V, I _D = 44 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		17	31	ns
t _r	Rise Time			7	15	
t _{d(off)}	Turn – Off Delay Time			25	40	
t _f	Fall Time			5	10	
Q _g	Total Gate Charge	V _{GS} = 0 V to 10 V, V _{DD} = 40 V, I _D = 44 A		40	56	nC
Q _g	Total Gate Charge			25	35	
Q _{gs}	Gate to Source Charge			13		
Q _{gd}	Gate to Drain "Miller" Charge			8		
Q _{oss}	Output Charge	V _{DD} = 40 V, V _{GS} = 0 V		60		nC
Q _{sync}	Output Charge	V _{DS} = 0 V, I _D = 44 A		35		

DRAIN-SOURCE DIODE CHARACTERISTICS

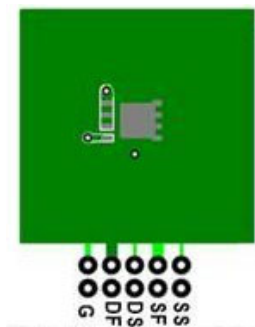
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.1 A (Note 2)		0.7	1.2	V
		V _{GS} = 0 V, I _S = 44 A (Note 2)		0.8	1.3	
t _{rr}	Reverse Recovery Time	I _F = 22 A, di/dt = 300 A/μs		26	42	ns
Q _{rr}	Reverse Recovery Charge			44	71	nC
t _{rr}	Reverse Recovery Time	I _F = 22 A, di/dt = 1000 A/μs		20	32	ns
Q _{rr}	Reverse Recovery Charge			106	169	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

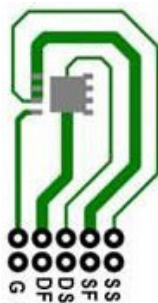
FDMS4D4N08C

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1 in² pad of 2 oz copper.



b) 125°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%.
3. E_{AS} of 486 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 3$ mH, $I_{AS} = 18$ A, $V_{DD} = 80$ V, $V_{GS} = 10$ V. 100% tested at $L = 0.1$ mH, $I_{AS} = 51$ A.
4. Pulsed I_D please refer to Figure 11 SOA graph for more details.
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

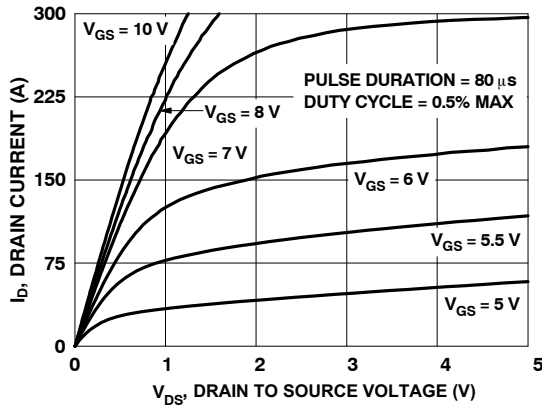


Figure 1. On Region Characteristics

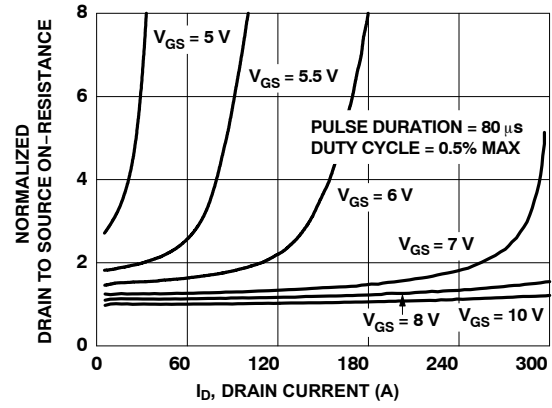


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

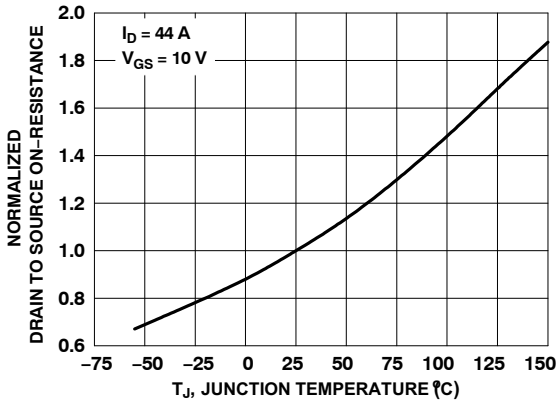


Figure 3. Normalized On Resistance vs. Junction Temperature

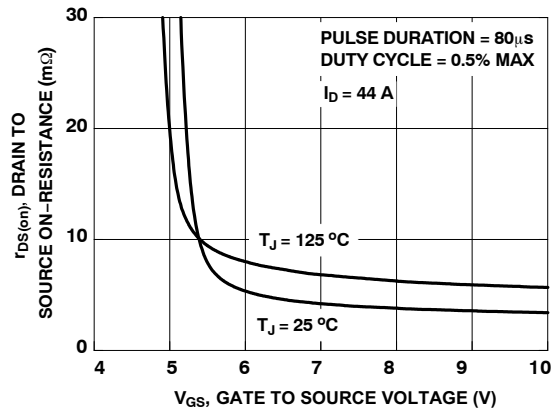


Figure 4. On-Resistance vs. Gate to Source Voltage

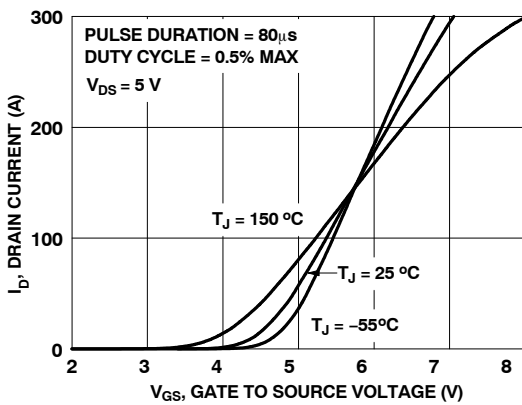


Figure 5. Transfer Characteristics

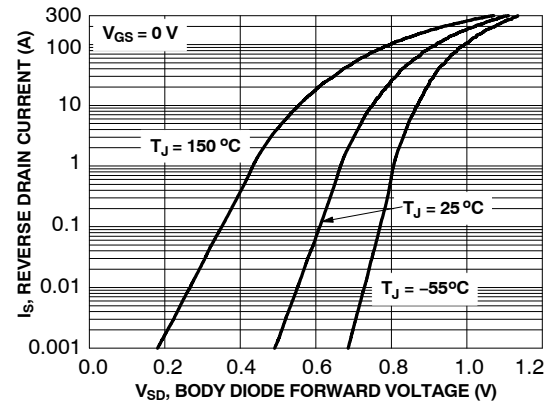


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (continued)

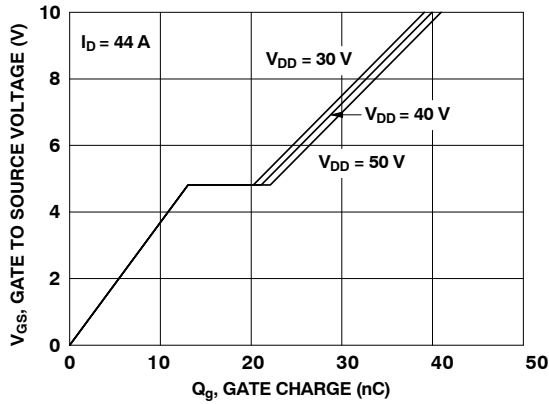


Figure 7. Gate Charge Characteristics

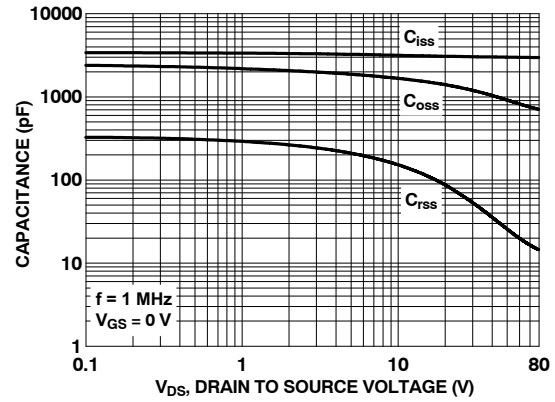


Figure 8. Capacitance vs. Drain to Source Voltage

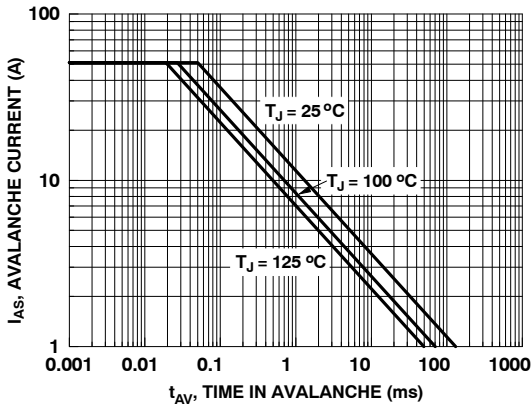


Figure 9. Unclamped Inductive Switching Capability

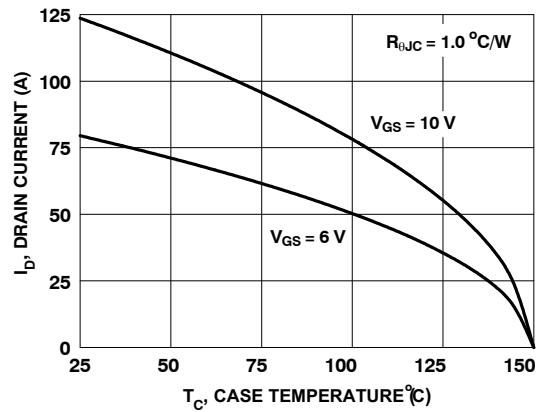


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

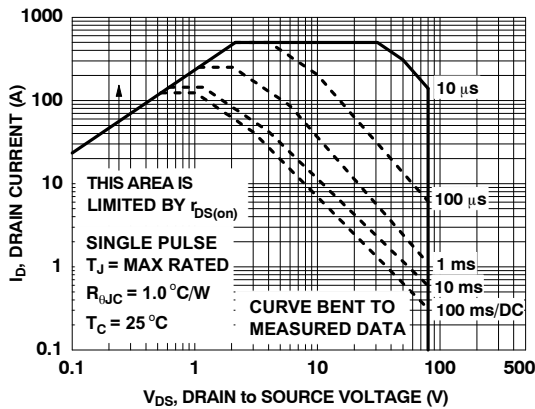


Figure 11. Forward Bias Safe Operating Area

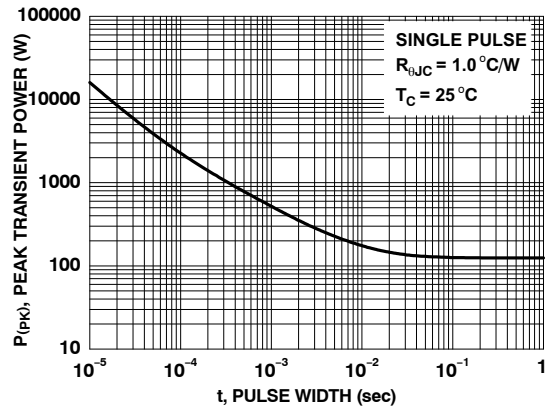


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (continued)

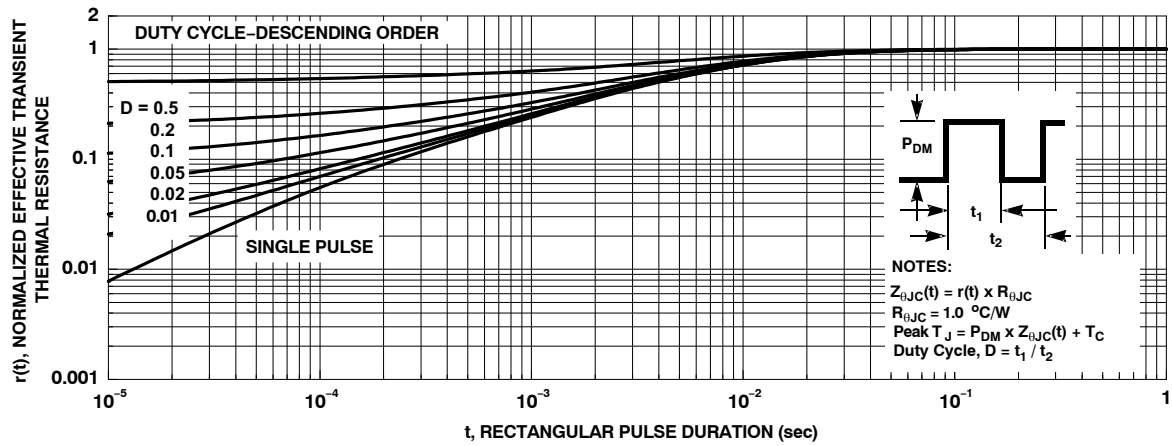
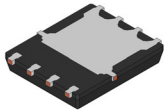
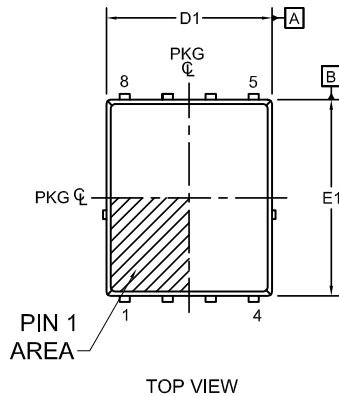


Figure 13. Junction-to-Case Transient Thermal Response Curve

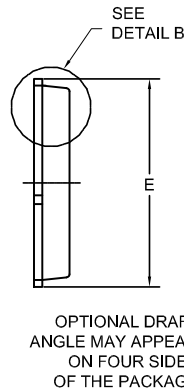


PQFN8 5X6, 1.27P
CASE 483AE
ISSUE C

DATE 21 JAN 2022



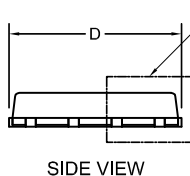
TOP VIEW



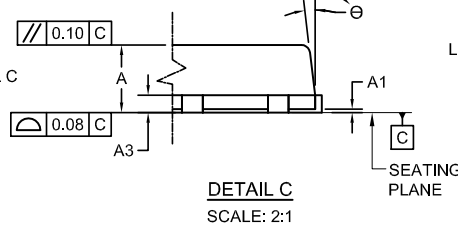
OPTIONAL DRAFT
ANGLE MAY APPEAR
ON FOUR SIDES
OF THE PACKAGE

NOTES:

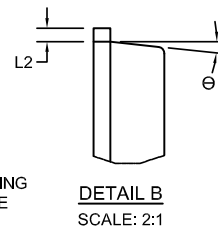
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



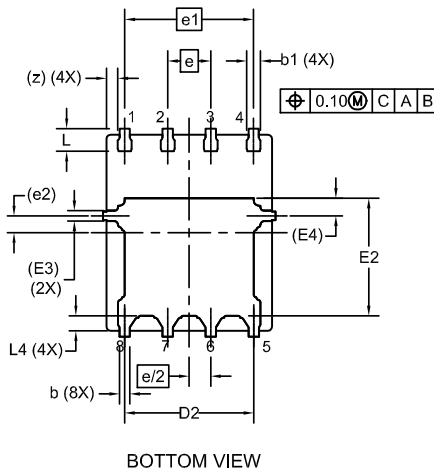
SIDE VIEW



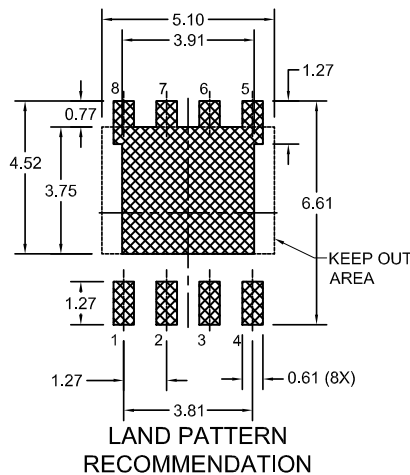
DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW



LAND PATTERN
RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	-	0.05
b	0.21	0.31	0.41
b1	0.31	0.41	0.51
A3	0.15	0.25	0.35
D	4.90	5.00	5.20
D1	4.80	4.90	5.00
D2	3.61	3.82	3.96
E	5.90	6.15	6.25
E1	5.70	5.80	5.90
E2	3.38	3.48	3.78
E3	0.30 REF		
E4	0.52 REF		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
e2	0.50 REF		
L	0.51	0.66	0.76
L2	0.05	0.18	0.30
L4	0.34	0.44	0.54
z	0.34 REF		
θ	0°	-	12°

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DESCRIPTION: PQFN8 5X6, 1.27P

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